

Common Anode Silicon Dual Switching Diodes

DAP222M3T5G

These Common Anode Silicon Epitaxial Planar Dual Diodes are designed for use in ultra high speed switching applications. The DAP222 device is housed in the SOT-723 package which is designed for low power surface mount applications, where board space is at a premium.

Features

- Fast t_{rr}
- Low C_D
- Available in 4 mm Tape and Reel
- This is a Pb-Free Device

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	80	V
Peak Reverse Voltage	V_{RM}	80	V
Forward Current	I_F	100	mA

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation	P_D	260	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

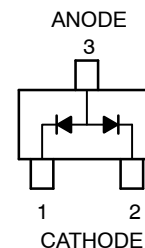
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. $t = 1.0 \mu\text{s}$.

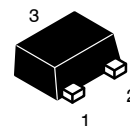


ON Semiconductor®

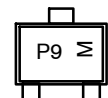
www.onsemi.com



MARKING DIAGRAM



SOT-723
CASE 631AA
STYLE 4



P9 = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
DAP222M3T5G	SOT-723 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

DAP222M3T5G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Characteristic	Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	I_R	$V_R = 70\text{ V}$	–	0.1	μA
Forward Voltage	V_F	$I_F = 100\text{ mA}$	–	1.2	V
Reverse Breakdown Voltage	V_R	$I_R = 100\text{ }\mu\text{A}$	80	–	V
Diode Capacitance	C_D	$V_R = 6.0\text{ V}, f = 1.0\text{ MHz}$	–	3.5	pF
Reverse Recovery Time	t_{rr} (Note 2)	$I_F = 5.0\text{ mA}, V_R = 6.0\text{ V}, R_L = 100\text{ }\Omega, I_{rr} = 0.1 I_R$	–	4.0	ns

2. t_{rr} Test Circuit for DAP222 in Figure 4.

TYPICAL ELECTRICAL CHARACTERISTICS

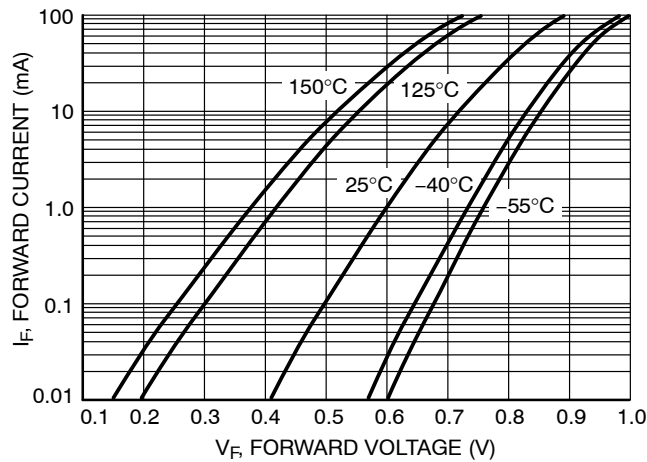


Figure 1. Forward Voltage

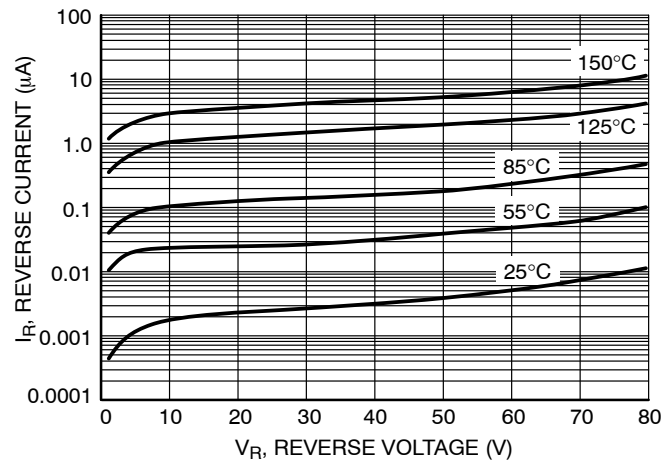


Figure 2. Reverse Current

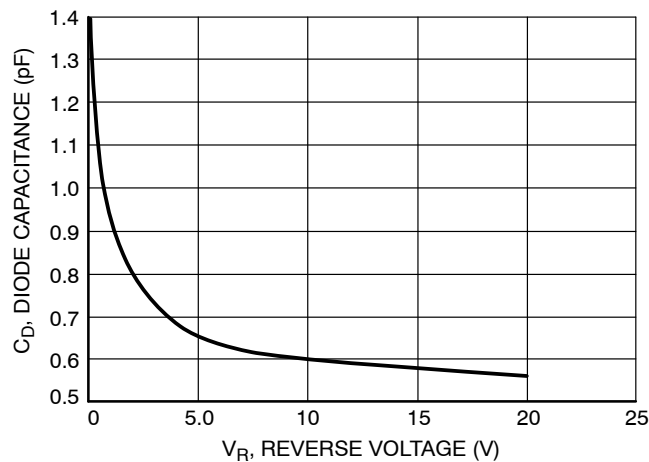
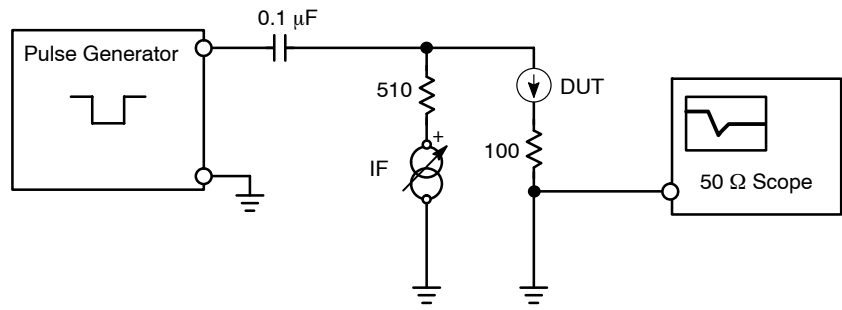
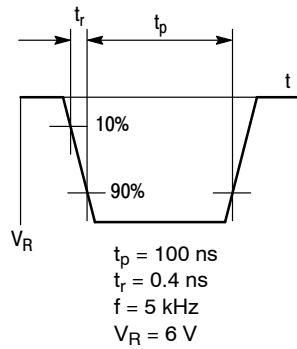


Figure 3. Diode Capacitance

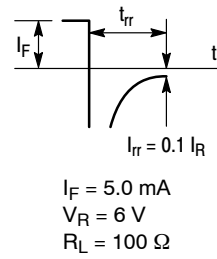
DAP222M3T5G



RECOVERY TIME EQUIVALENT TEST CIRCUIT



INPUT PULSE



OUTPUT PULSE

Figure 4. Reverse Recovery Time Test Circuit



SOT-723 1.20x0.80x0.50, 0.40P
CASE 631AA
ISSUE E

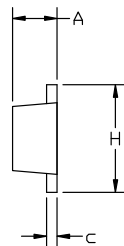
DATE 24 JAN 2024

NOTES:

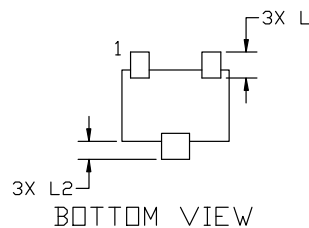
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



TOP VIEW



SIDE VIEW



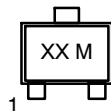
BOTTOM VIEW

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
c	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25



RECOMMENDED MOUNTING
FOOTPRINT

**GENERIC
MARKING DIAGRAM***



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN
---	--	--	--	--

DOCUMENT NUMBER:	98AON12989D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-723 1.20x0.80x0.50, 0.40P	PAGE 1 OF 1

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales